



**Datasheet**

**LCA-S-400K-SI**

**Low Noise 400 kHz Photoreceiver with Si PIN Photodiode**



The photoreceiver will be delivered without post holder and post

Features	<ul style="list-style-type: none"> <li>• <b>Large Area Si PIN Detector, 2.5 mm Active Diameter</b></li> <li>• <b>Spectral Range 400 ... 1100 nm</b></li> <li>• <b>Amplifier Transimpedance Gain <math>1.0 \times 10^7</math> V/A</b></li> <li>• <b>Max. Conversion Gain <math>6.2 \times 10^6</math> V/W @ 900 nm</b></li> <li>• <b>Bandwidth DC ... 400 kHz</b></li> </ul>																																												
Applications	<ul style="list-style-type: none"> <li>• <b>Spectroscopy</b></li> <li>• <b>General Purpose Opto-Electronic Measurements</b></li> <li>• <b>Optical Front-End for Oscilloscopes, A/D Converters and Lock-In Amplifiers</b></li> </ul>																																												
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## Low Noise 400 kHz Photoreceiver with Si PIN Photodiode

Specifications (continued)	
Output	Output Voltage Range $\pm 10$ V                            (@ $\geq 1$ M $\Omega$ load) Max. Output Current $\pm 30$ mA Output Impedance                50 $\Omega$ (designed for $\geq 1$ M $\Omega$ load) Output Noise                        ca. 10 mV peak-peak or 1.5 mV rms (@ $\geq 1$ M $\Omega$ load, no signal on detector)
Power Supply	Supply Voltage $\pm 15$ V Supply Current $\pm 40$ mA typ. (depends on operating conditions, recommended power supply capability minimum $\pm 150$ mA)
Case	Weight                                210 g (0.5 lbs) Material                                AlMg4.5Mn, nickel-plated
Temperature Range	Storage Temperature            - 40 ... + 100 °C Operating Temperature        0 ... + 60 °C
Absolute Maximum Ratings	Optical Input Power            10 mW Power Supply Voltage $\pm 22$ V



